



Digital Integrated Circuits

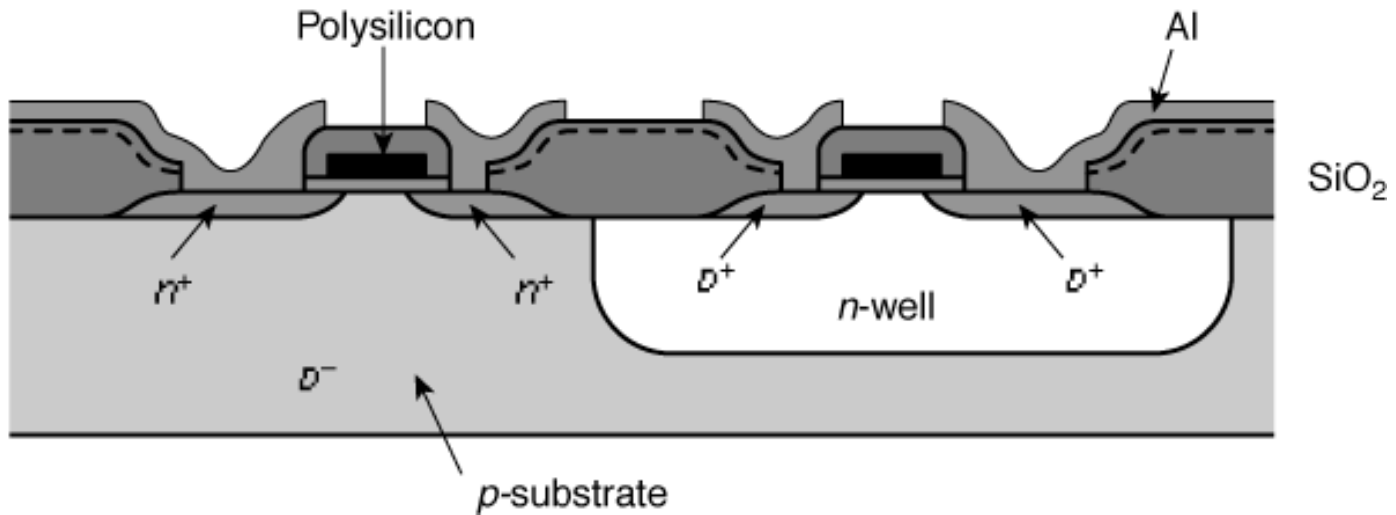
A Design Perspective

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Anantha Chandrakasan
Borivoje Nikolic

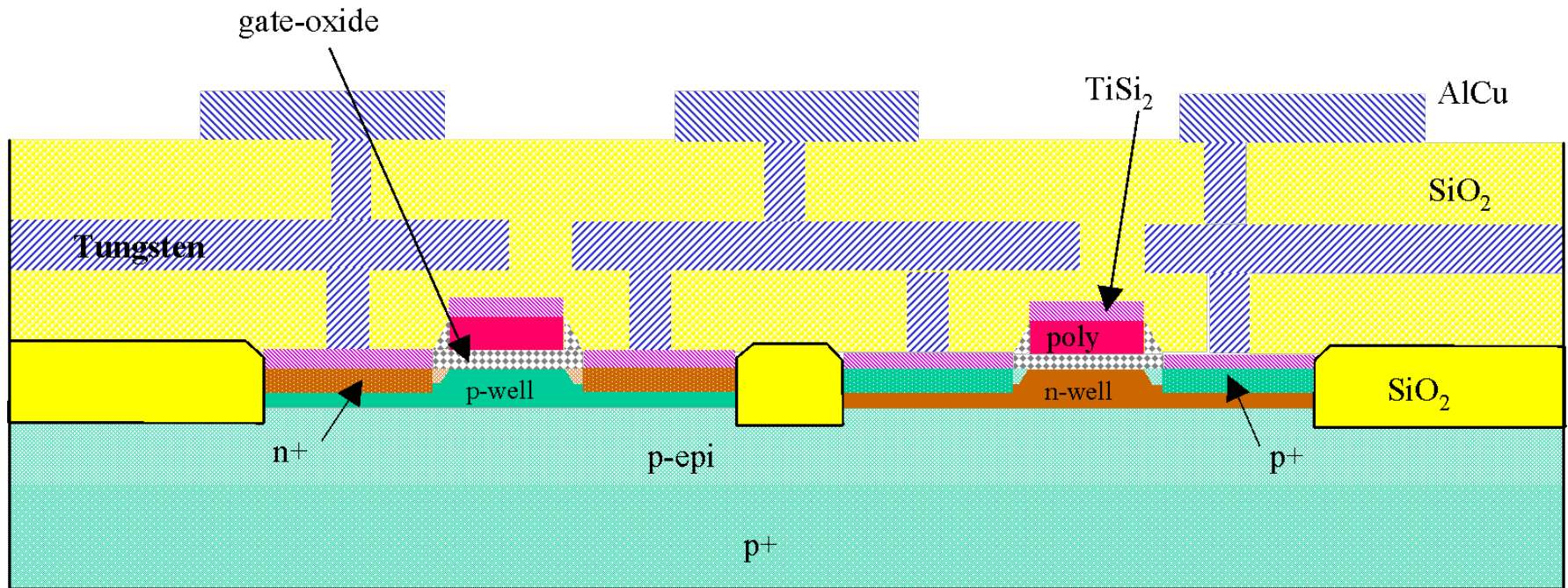
Manufacturing Process

July 30, 2002

CMOS Process

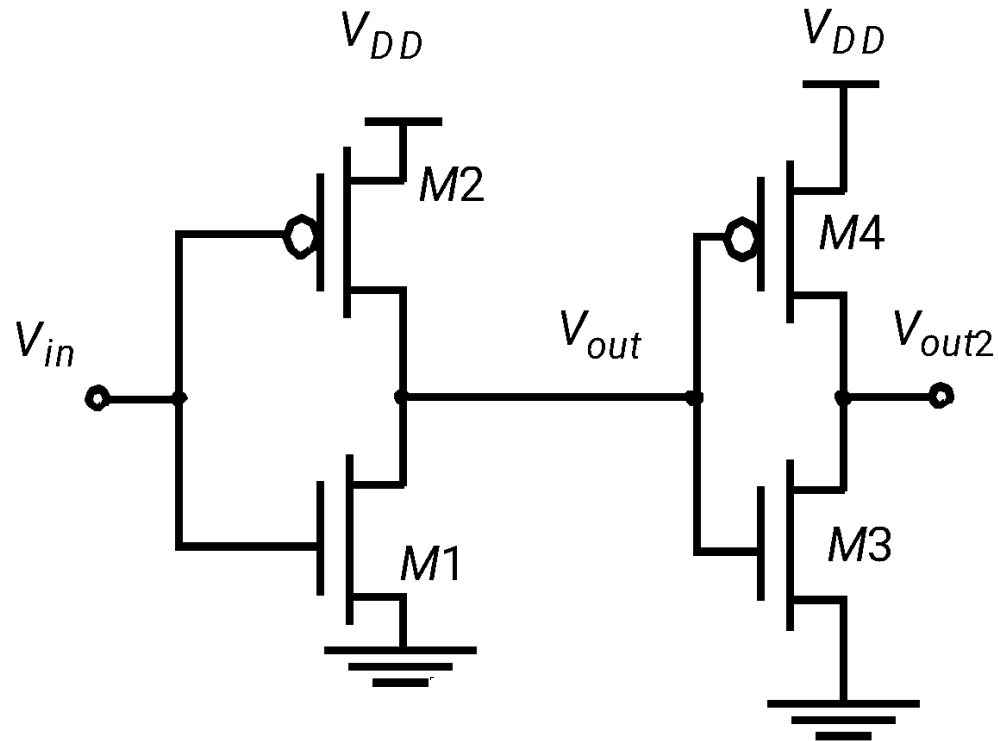


A Modern CMOS Process

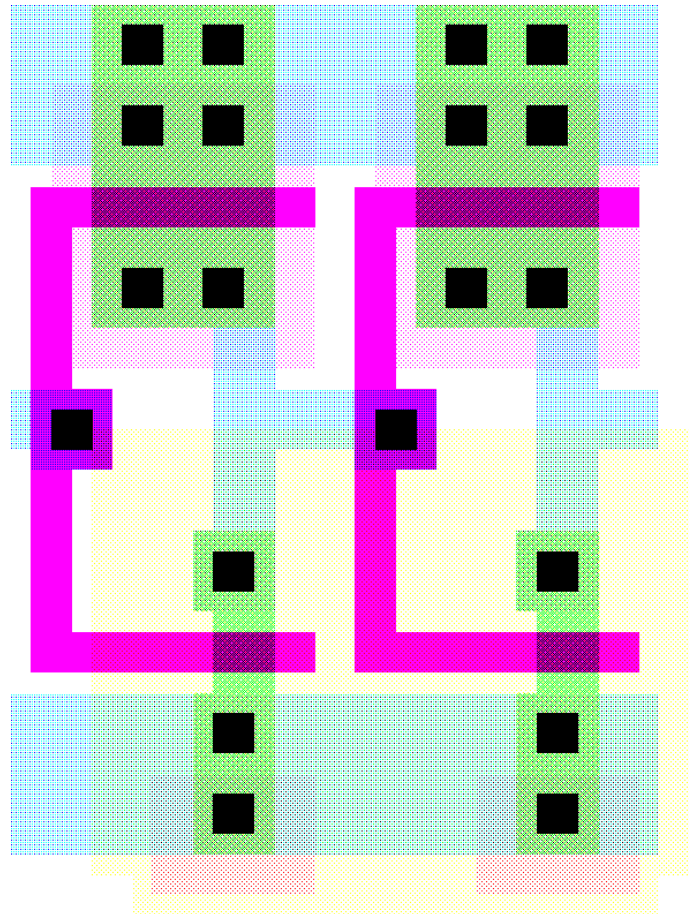


Dual-Well Trench-Isolated CMOS Process

Circuit Under Design



Its Layout View

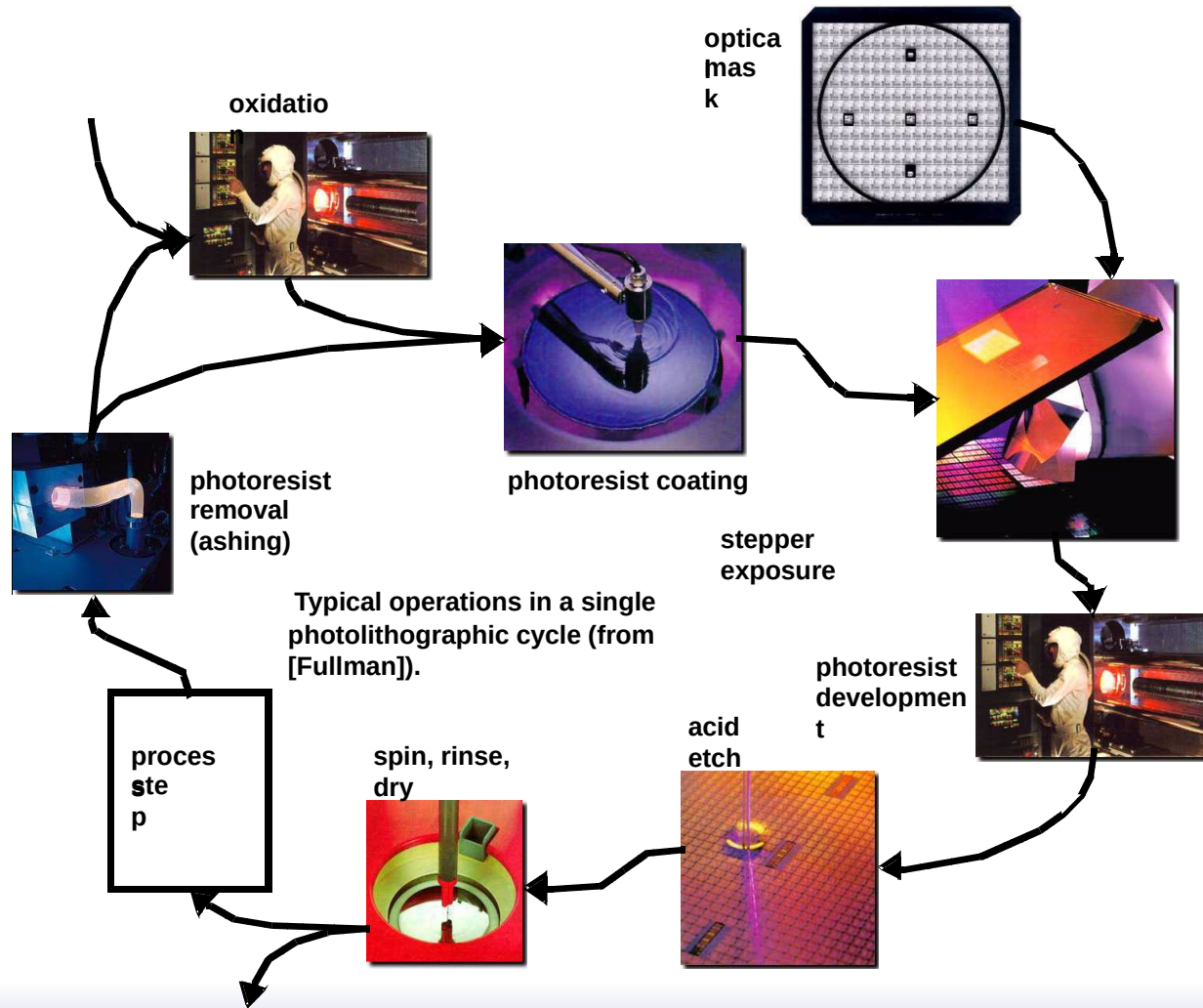


The Manufacturing Process

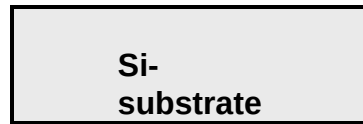
For a great tour through the IC manufacturing process and its different steps, check

[http://www.fullman.com/semiconductors/
semiconductors.html](http://www.fullman.com/semiconductors/semiconductors.html)

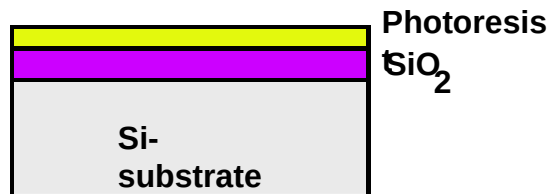
Photo-Lithographic Process



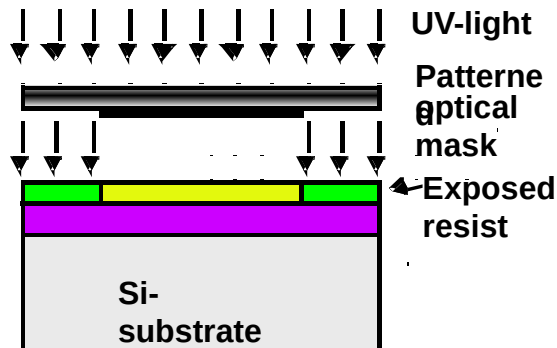
Patterning of SiO₂



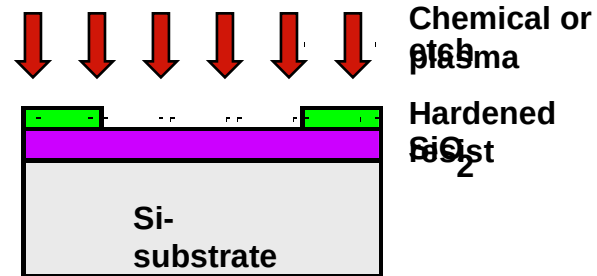
(a) Silicon base material



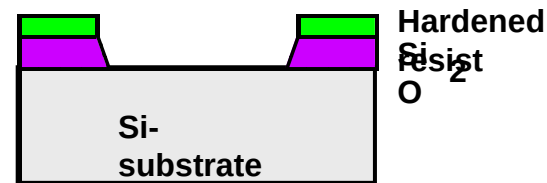
(b) After oxidation and deposition of negative photoresist



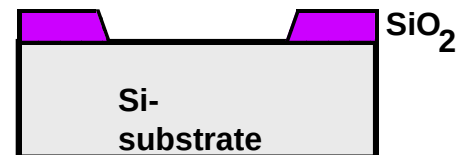
(c) Stepper exposure



(d) After development and etching of resist, chemical or plasma etch of SiO₂

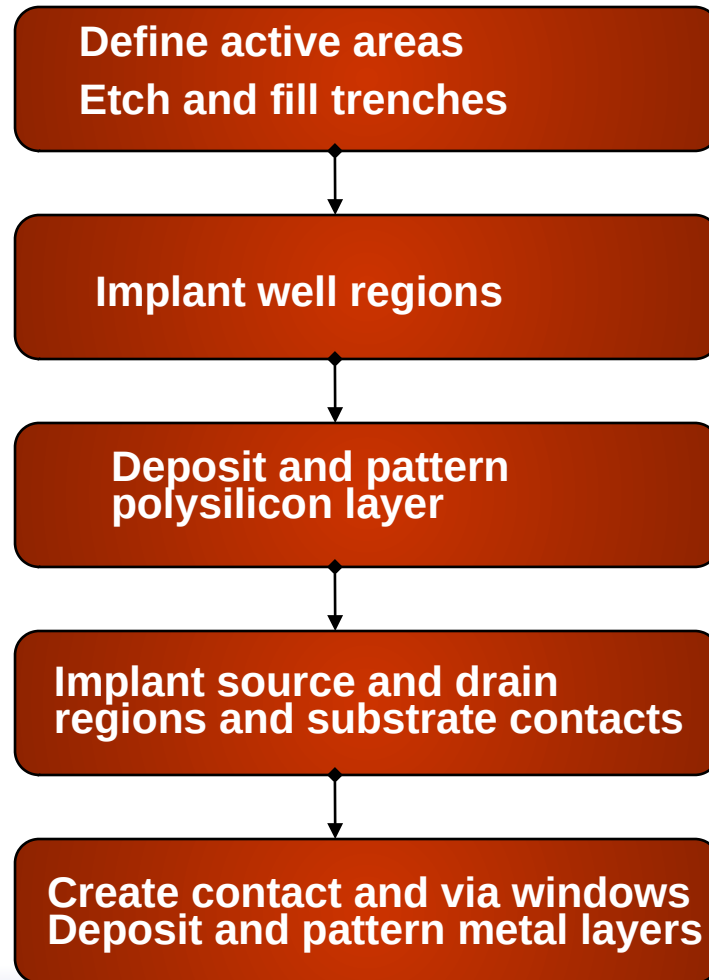


(e) After etching

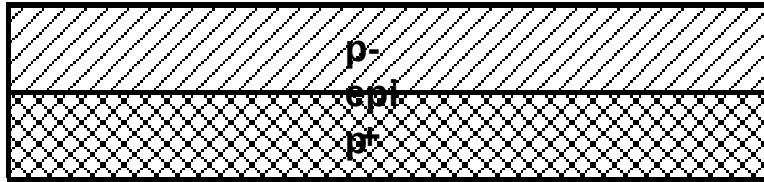


(f) Final result after removal of resist

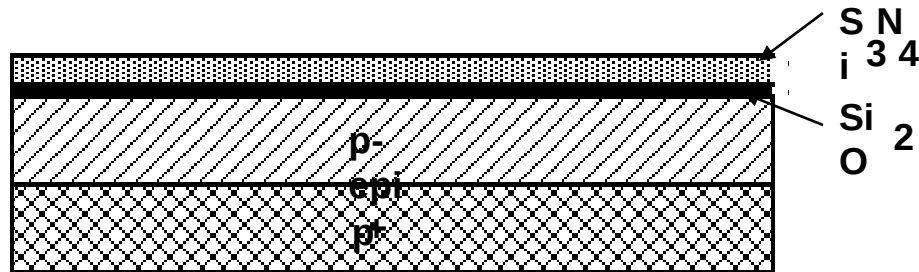
CMOS Process at a Glance



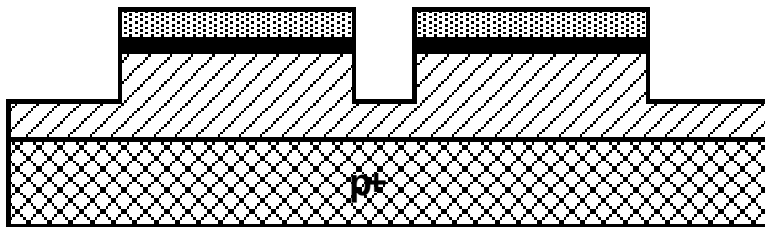
CMOS Process Walk-Through



(a) Base material: p+ substrate with p-epi layer

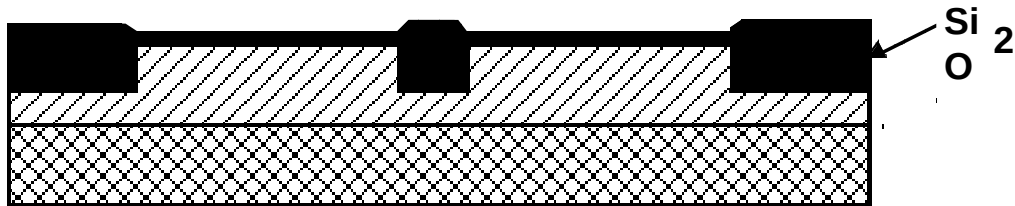


(b) After deposition of gate-oxide and sacrificial nitride (acts as buffer layer)

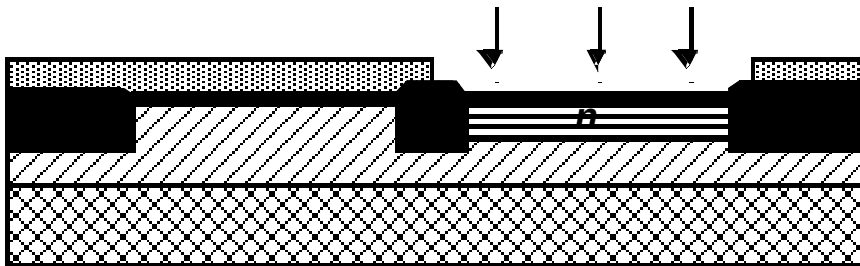


(c) After plasma etch of trenches using the inverse of the active area mask

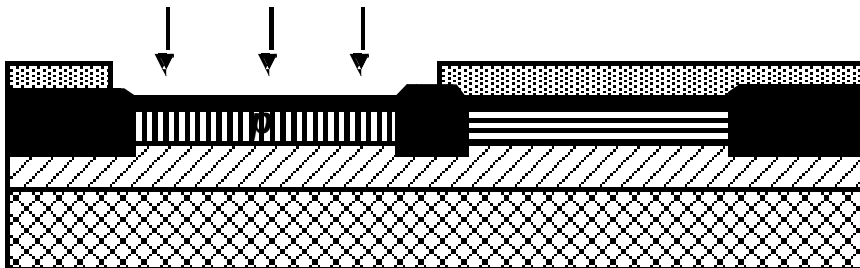
CMOS Process Walk-Through



(d) After trench filling, planarization, and removal of sacrificial nitride

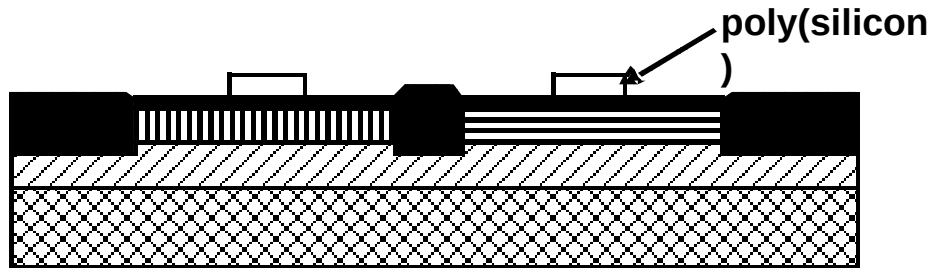


(e) After n-well and V_T adjust p implants

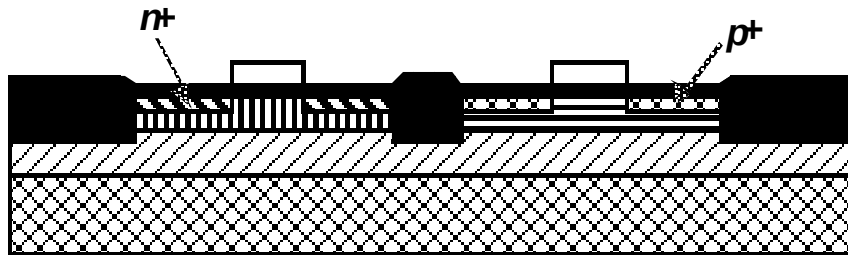


(f) After p-well and adjust n implants

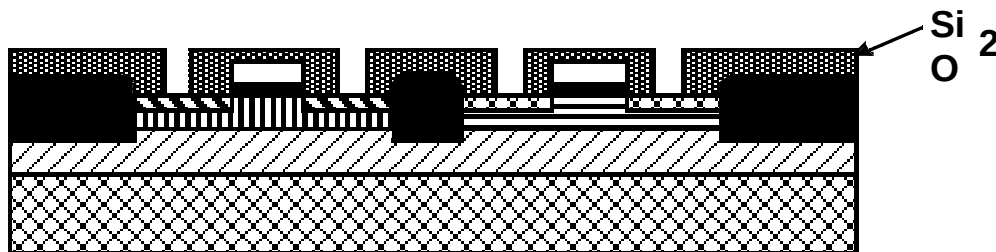
CMOS Process Walk-Through



(g) After polysilicon deposition and etch

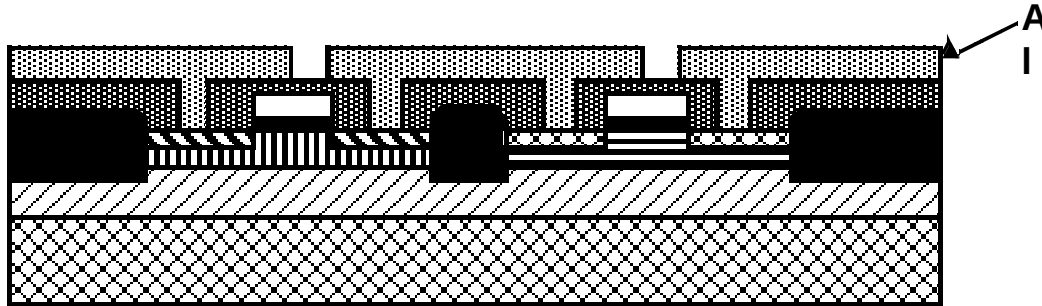


(h) After n^+ source/drain and p^+ source/drain implants. These steps also dope the polysilicon.

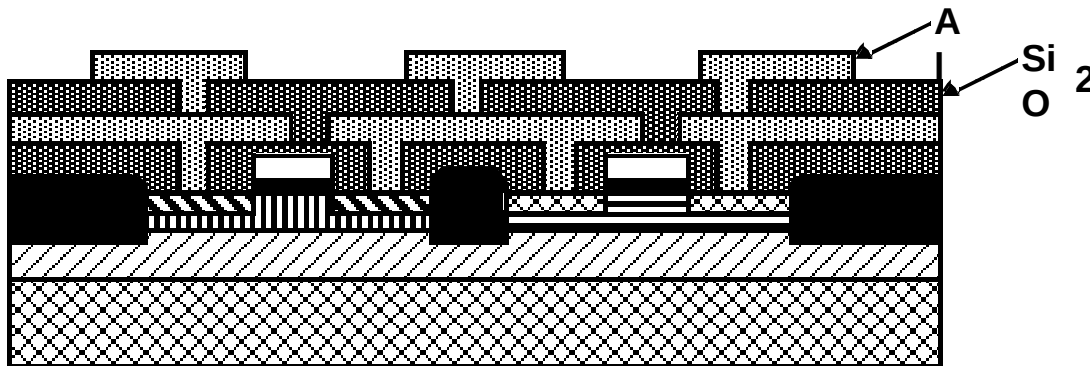


(i) After deposition of SiO_2 and contact hole etch.

CMOS Process Walk-Through

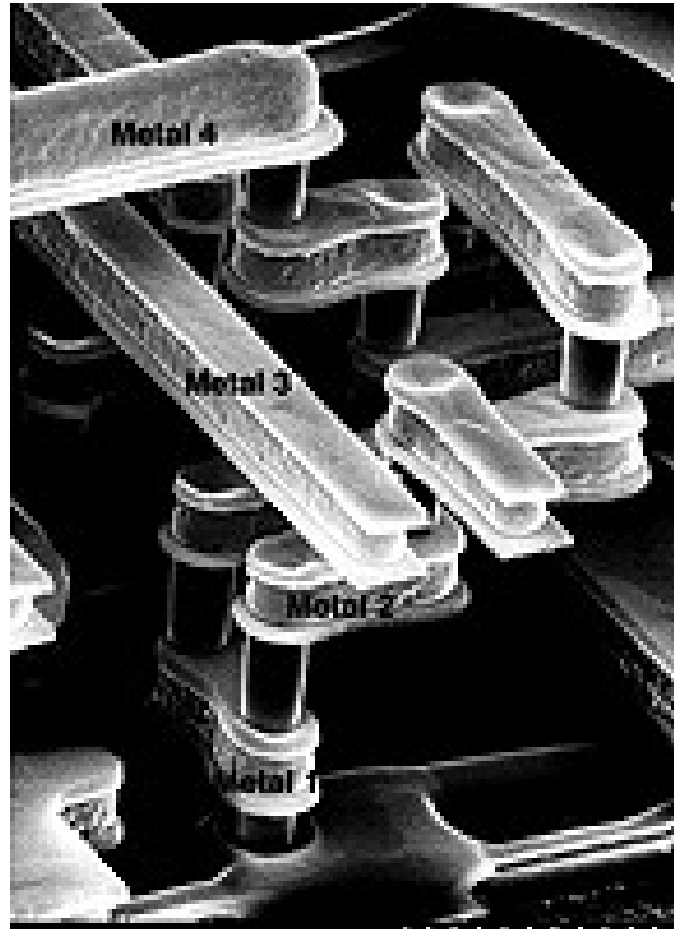


(j) After deposition and patterning of first Al layer.



(k) After deposition of insulator, etching of SiO_2 deposition and patterning of second layer of Al.

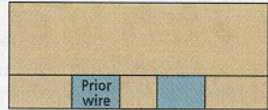
Advanced Metallization



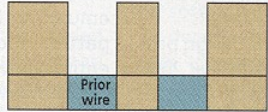
Advanced Metallization

Dual damascene IC process

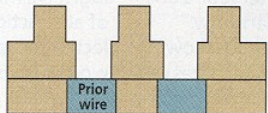
- Oxide deposition



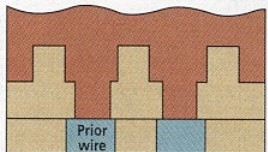
- Stud lithography and reactive ion etch



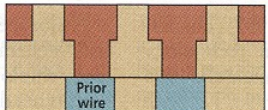
- Wire lithography and reactive ion etch



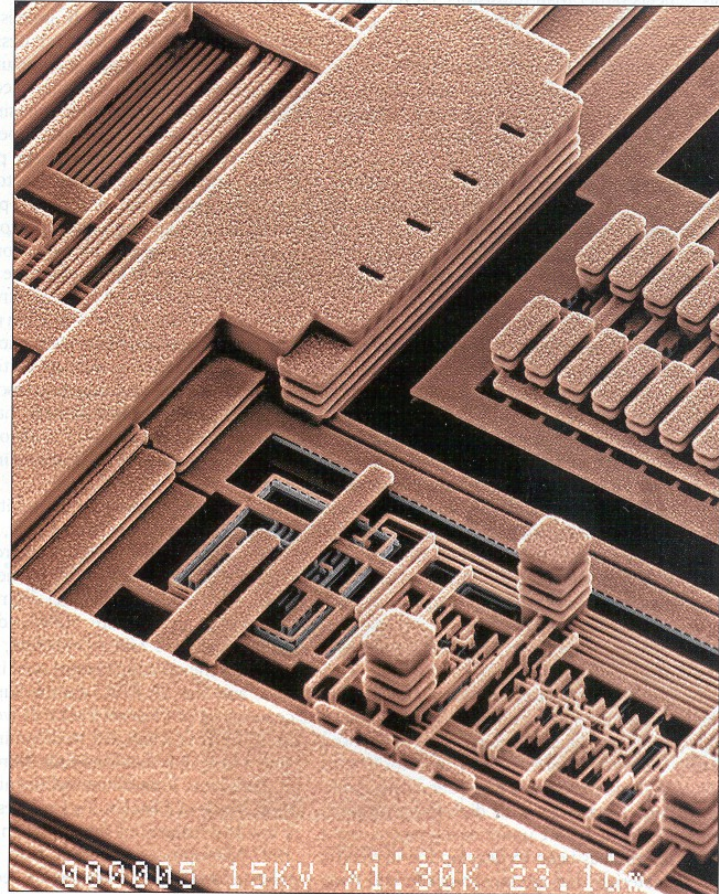
- Stud and wire metal deposition



- Metal chemical-mechanical polish



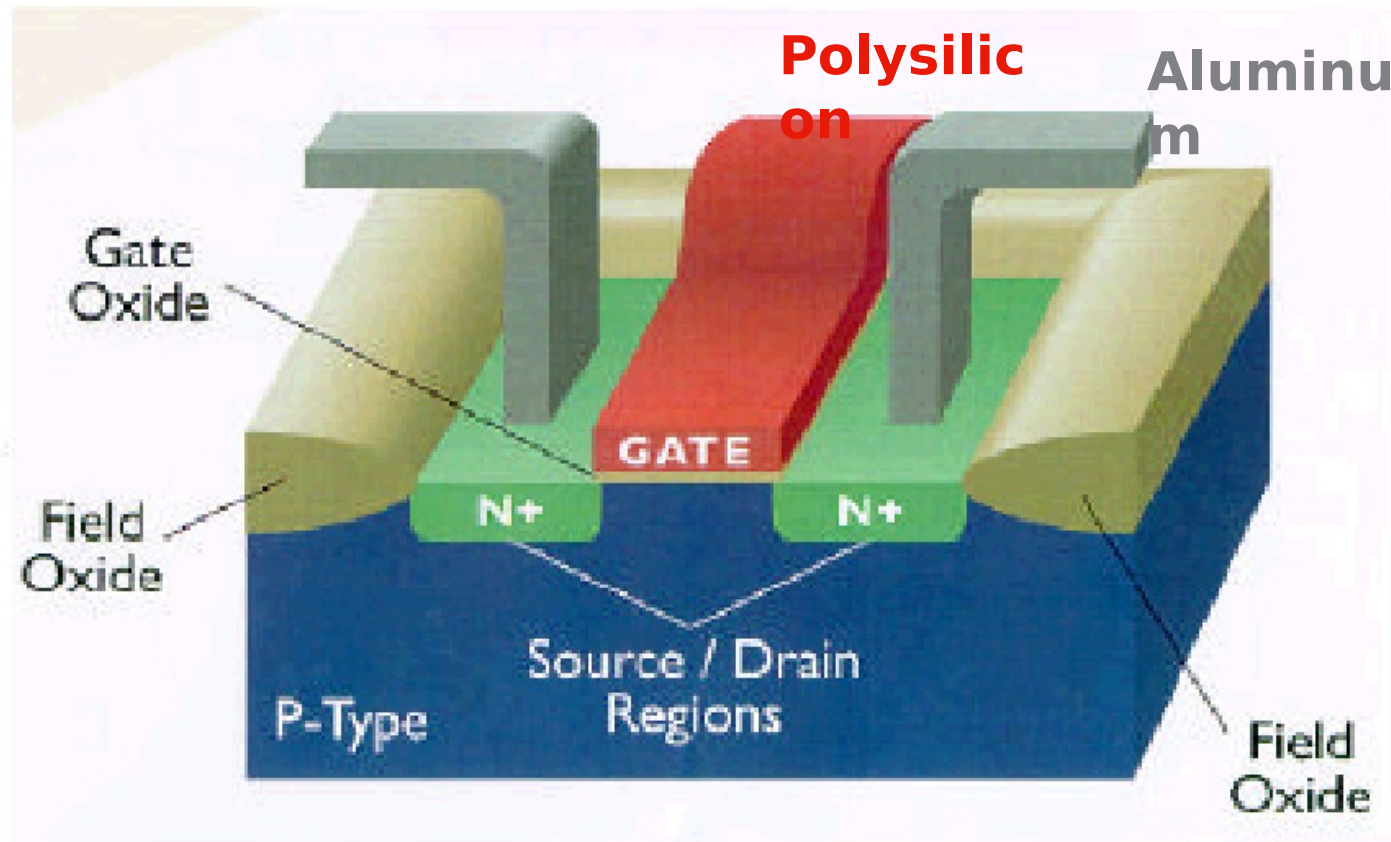
Source: IBM Corp.





Design Rules









3D Perspective







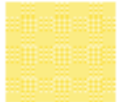


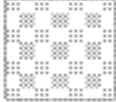
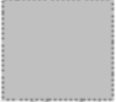









Design Rules

- ☐ Interface between designer and process engineer
- ☐ Guidelines for constructing process masks
- ☐ Unit dimension: Minimum line width
 - scalable design rules: lambda parameter
 - absolute dimensions (micron rules)

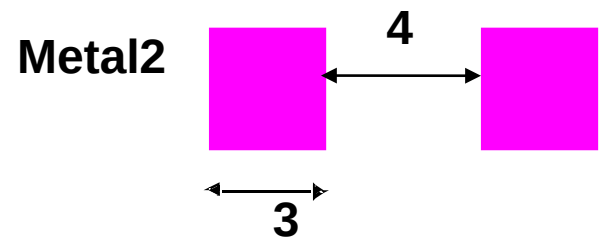
CMOS Process Layers

Layer	Color	Representation
Well (p,n)	Yellow	
Active Area (n+,p+)	Green	
Select (p+,n+) Polysilicon	Green	
Metal1	Red	
Metal2	Blue	
Contact To Poly	Magenta	
Contact To Diffusion	Black	
Via	Black	

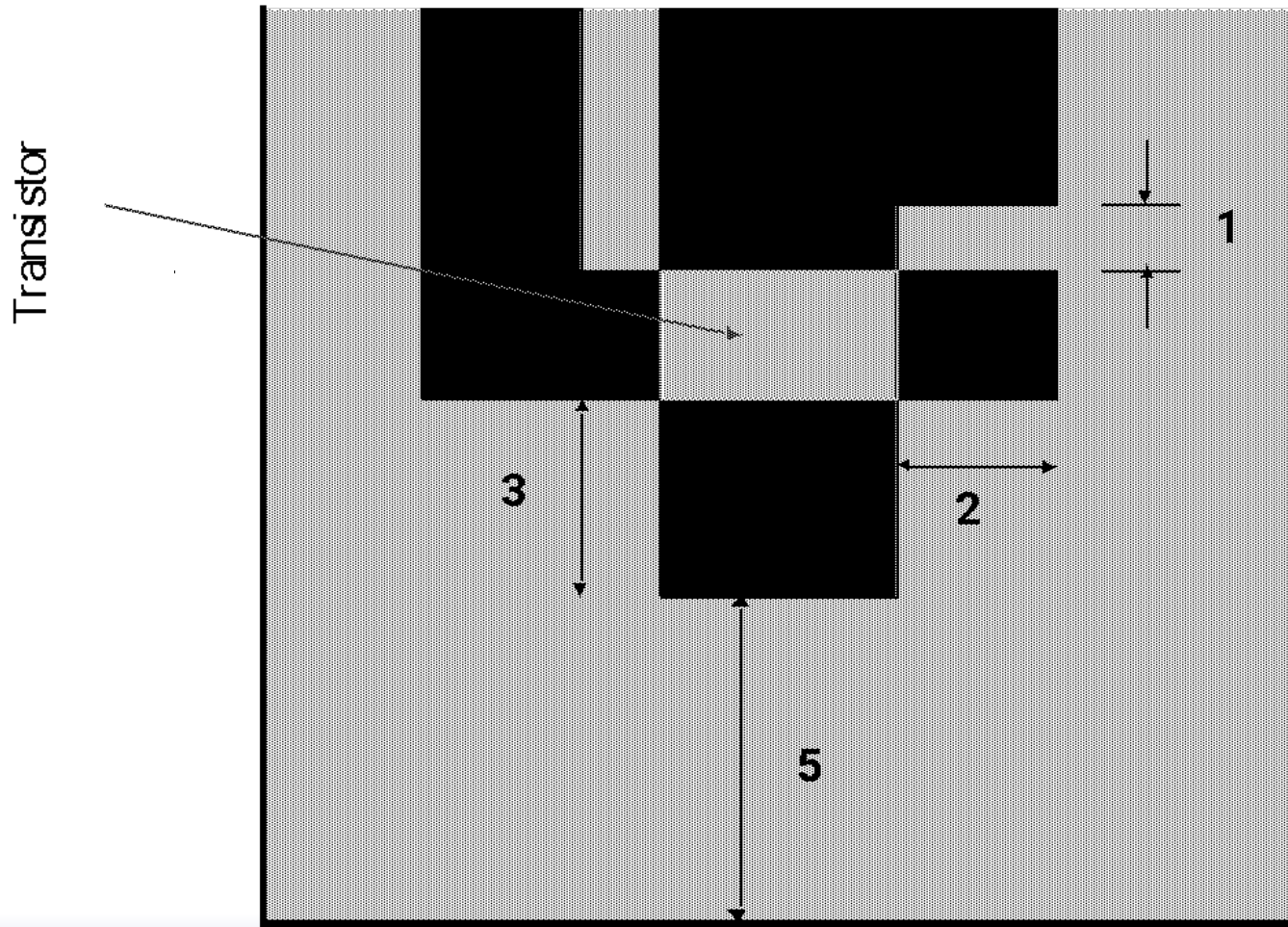
Layers in 0.25 μm CMOS process

Layer Description	Representation				
metal					
	m1	m2	m3	m4	m5
					
	nw				
					
polysilicon	poly				
contacts & vias					
	ct	v12,v23,v34,v45	nwc	pwc	
					
	ndif	pdif	nfet	pfet	
select					
	nplus	pplus	prb		

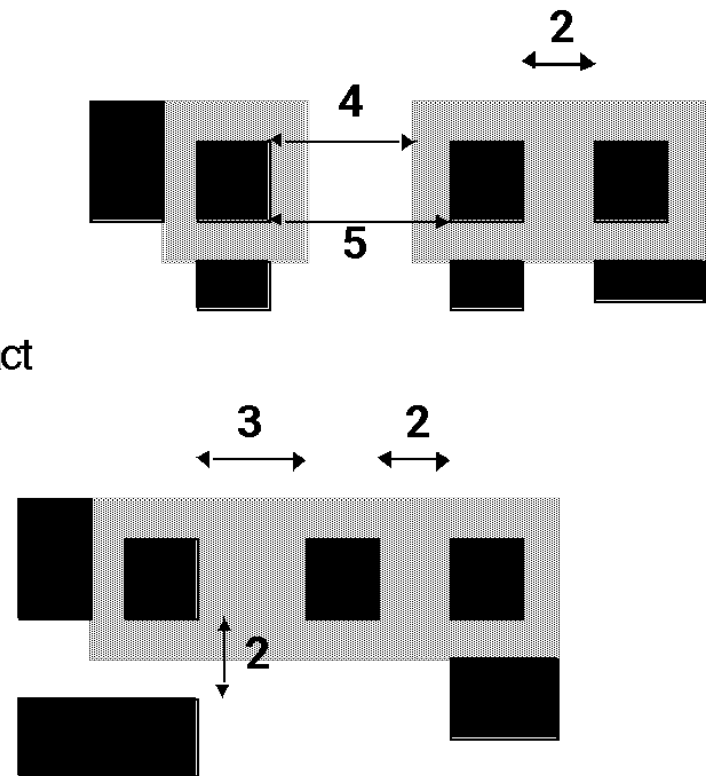
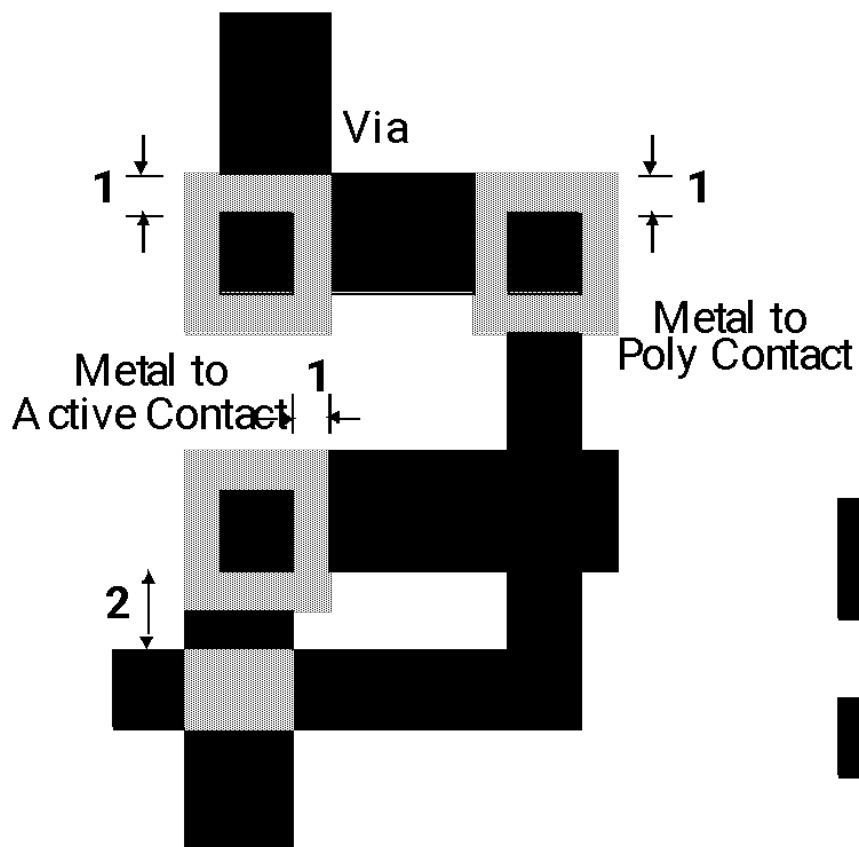
Intra-Layer Design Rules



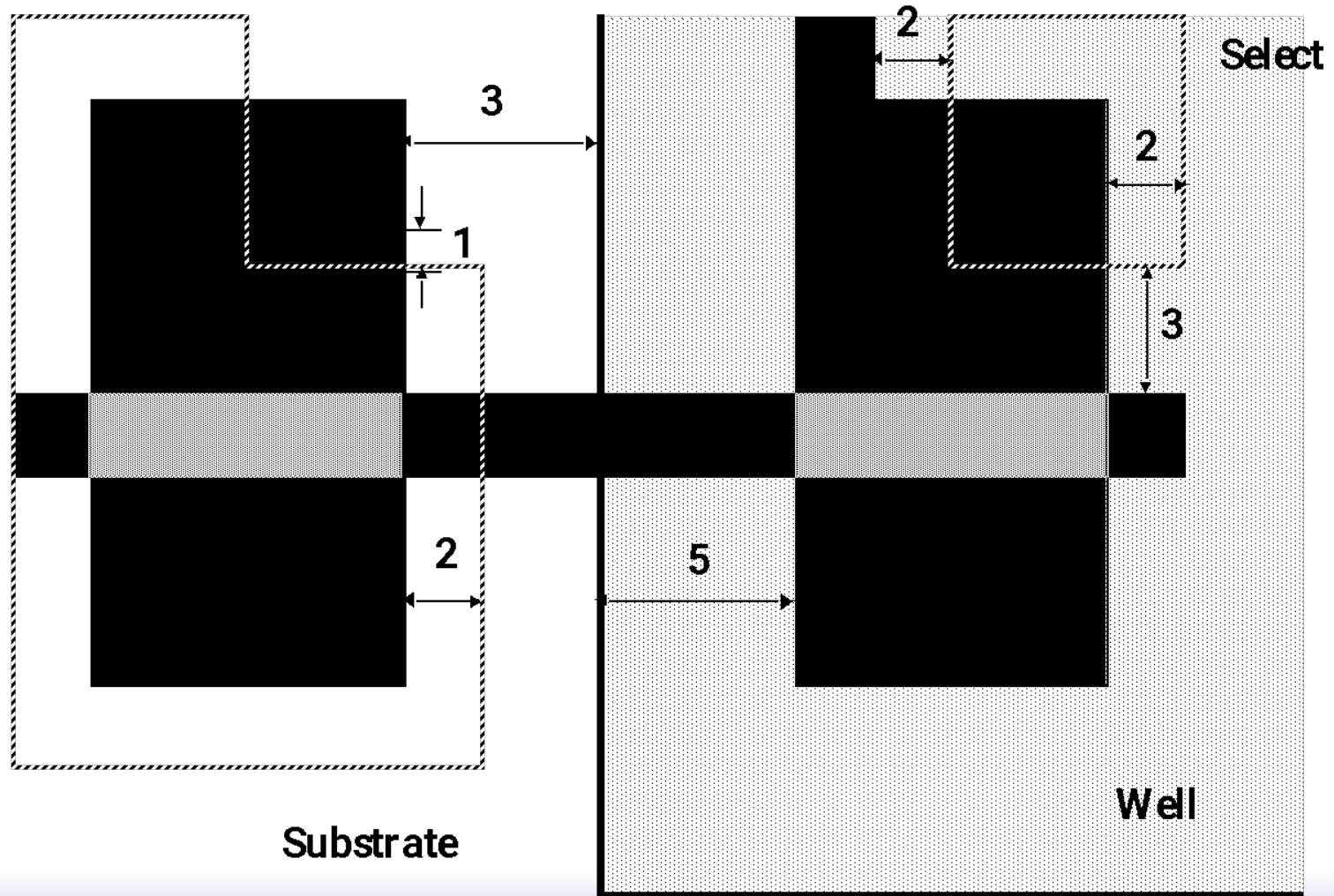
Transistor Layout



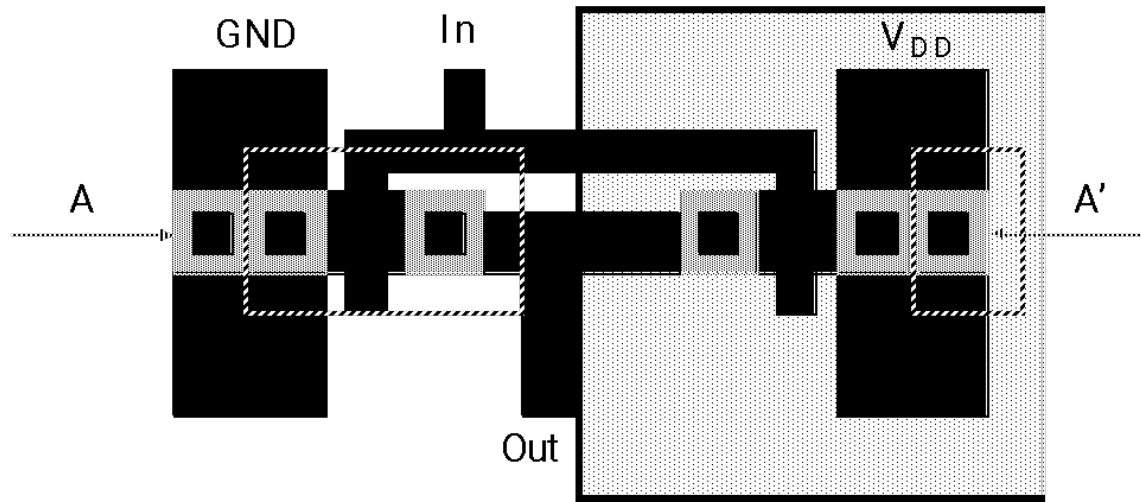
Vias and Contacts



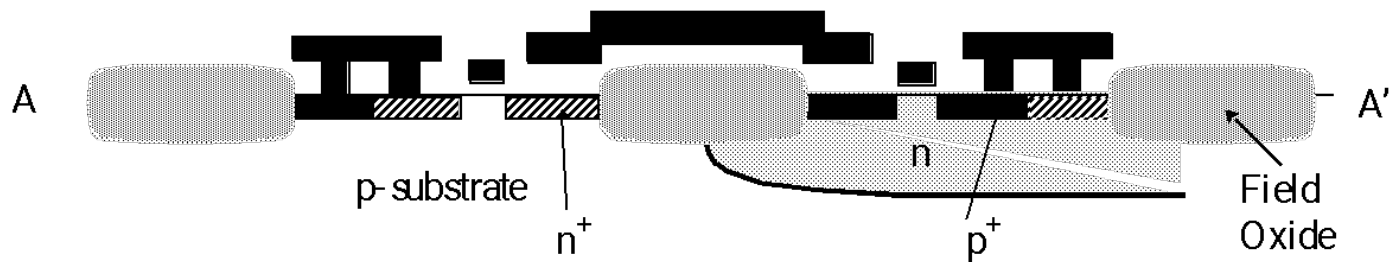
Select Layer



CMOS Inverter Layout

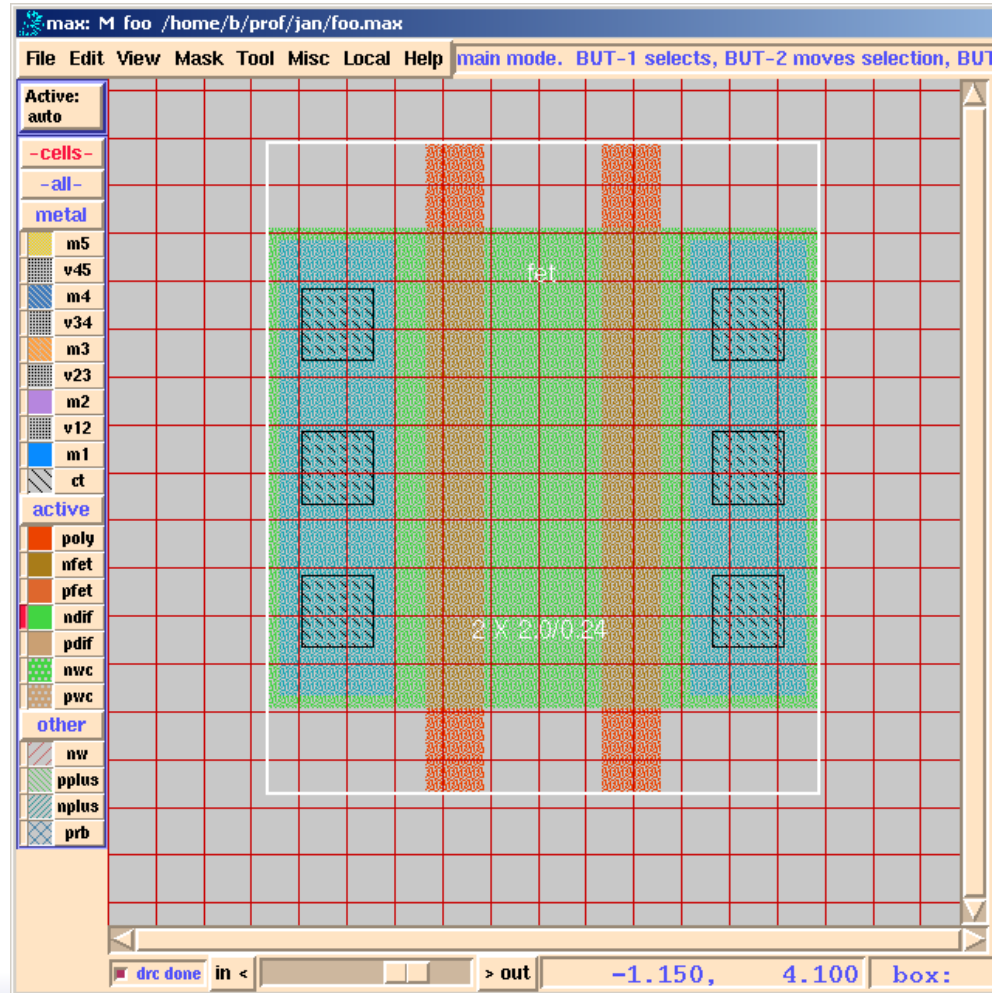


(a) Layout

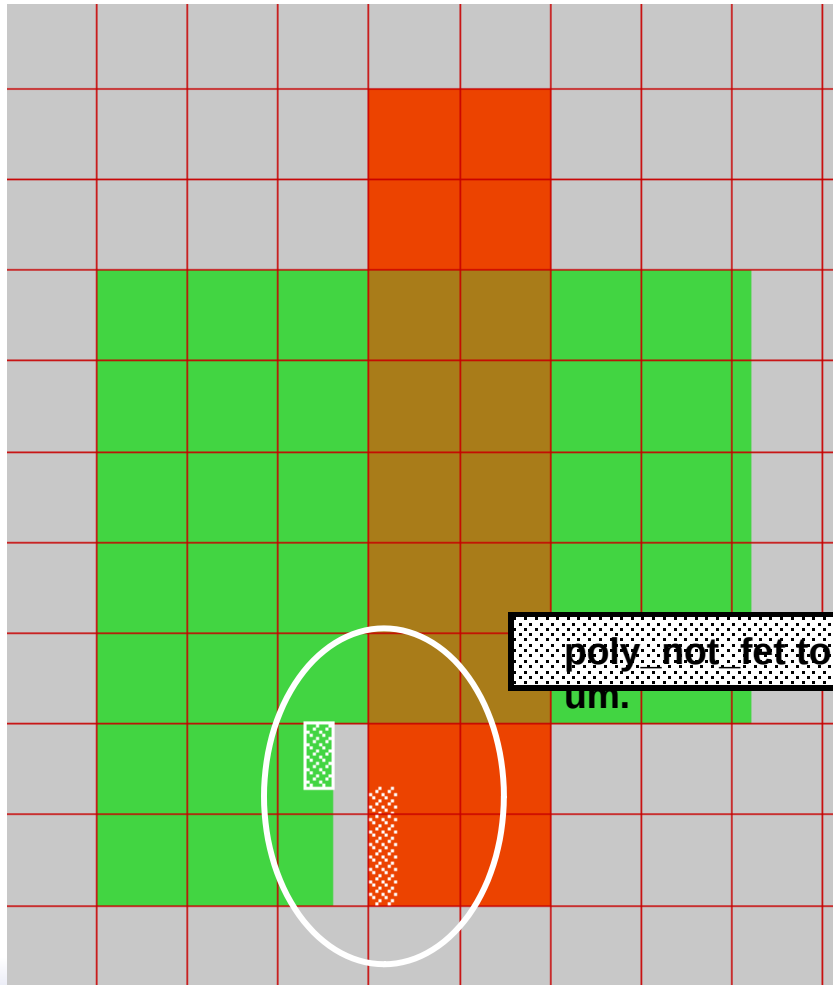


(b) Cross-Section along A-A'

Layout Editor

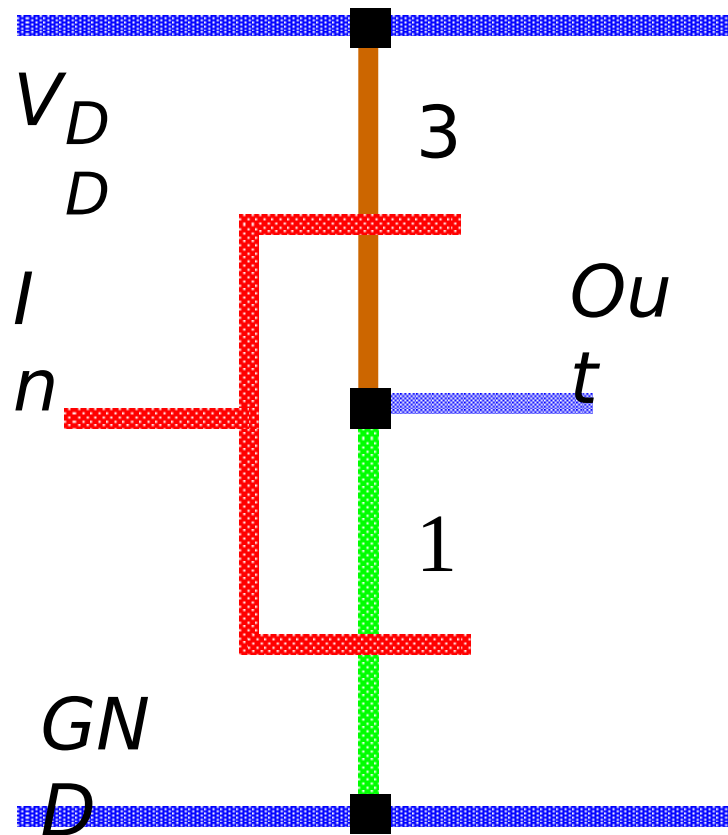


Design Rule Checker



poly not fet to all diff minimum spacing = 0.14
um.

Sticks Diagram



- Dimensionless layout entities
- Only topology is important
- Final layout generated by “compaction” program

**Stick diagram of
inverter**



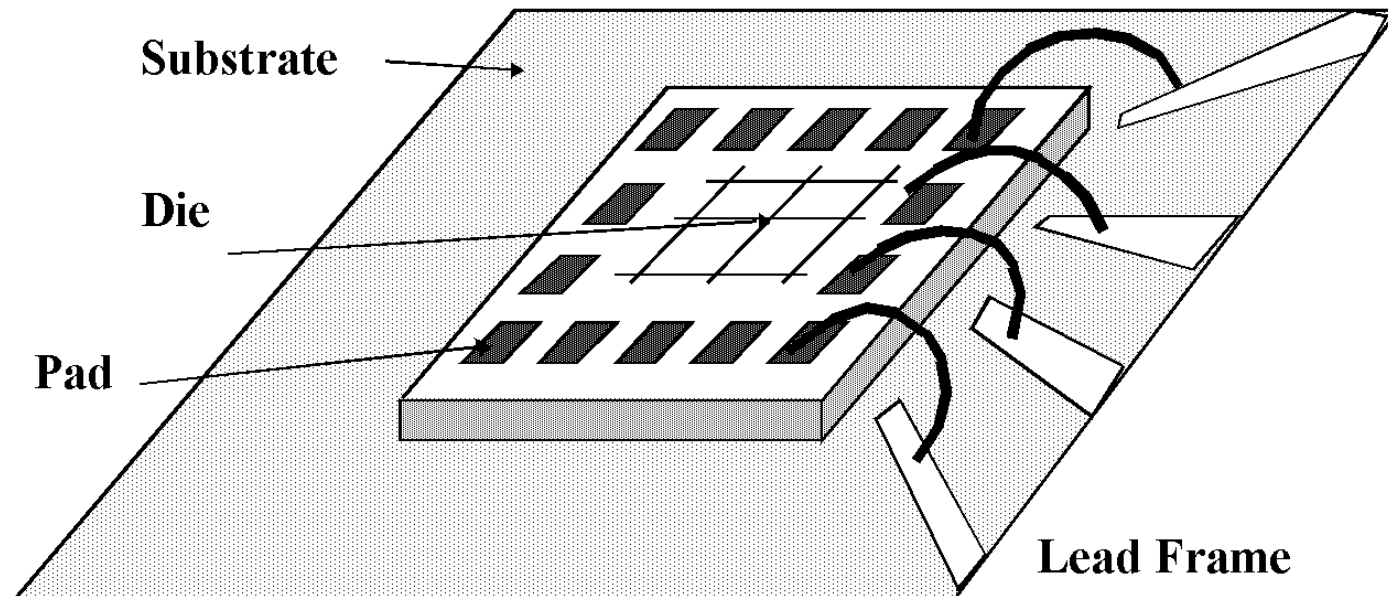
Packaging

Packaging Requirements

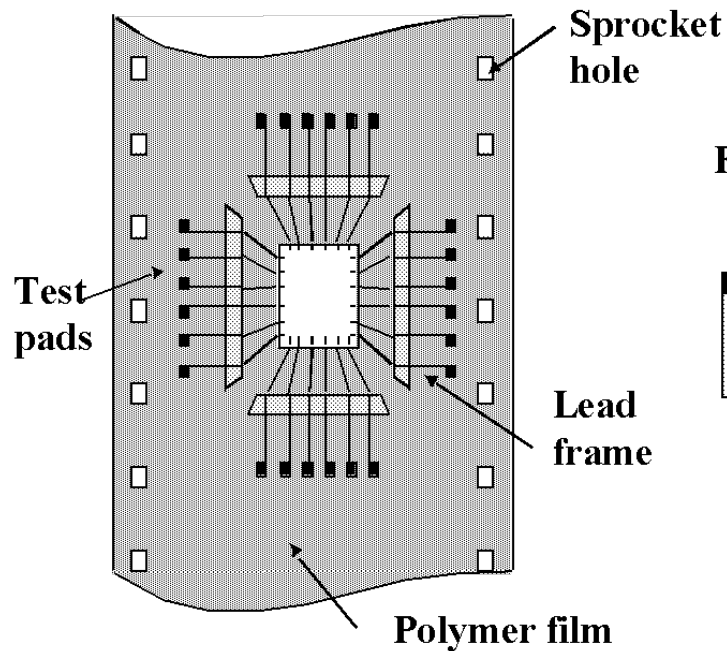
- ☐ **Electrical: Low parasitics**
- ☐ **Mechanical: Reliable and robust**
- ☐ **Thermal: Efficient heat removal**
- ☐ **Economical: Cheap**

Bonding Techniques

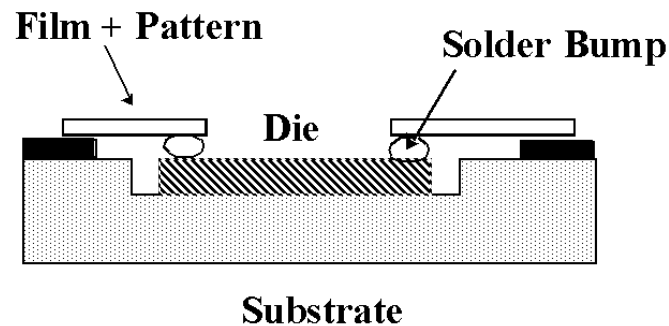
Wire Bonding



Tape-Automated Bonding (TAB)

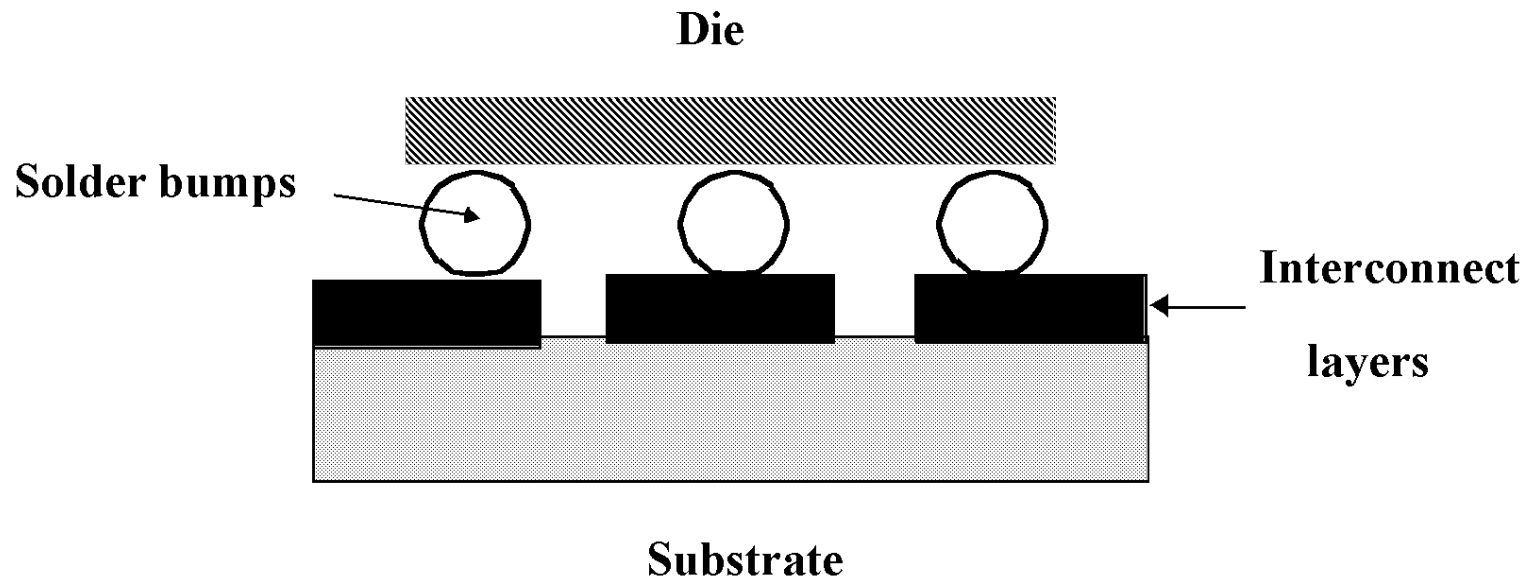


(a) Polymer Tape with imprinted wiring pattern.

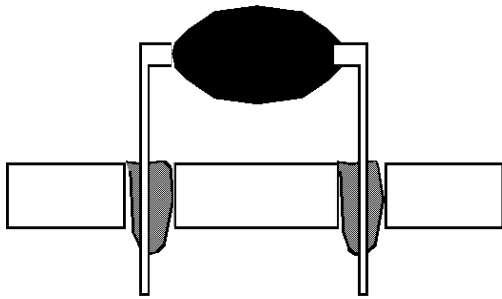


(b) Die attachment using solder bumps.

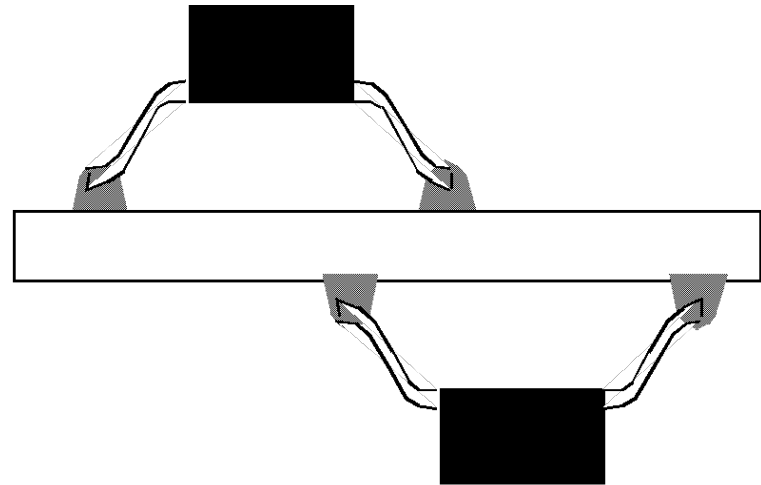
Flip-Chip Bonding



Package-to-Board Interconnect

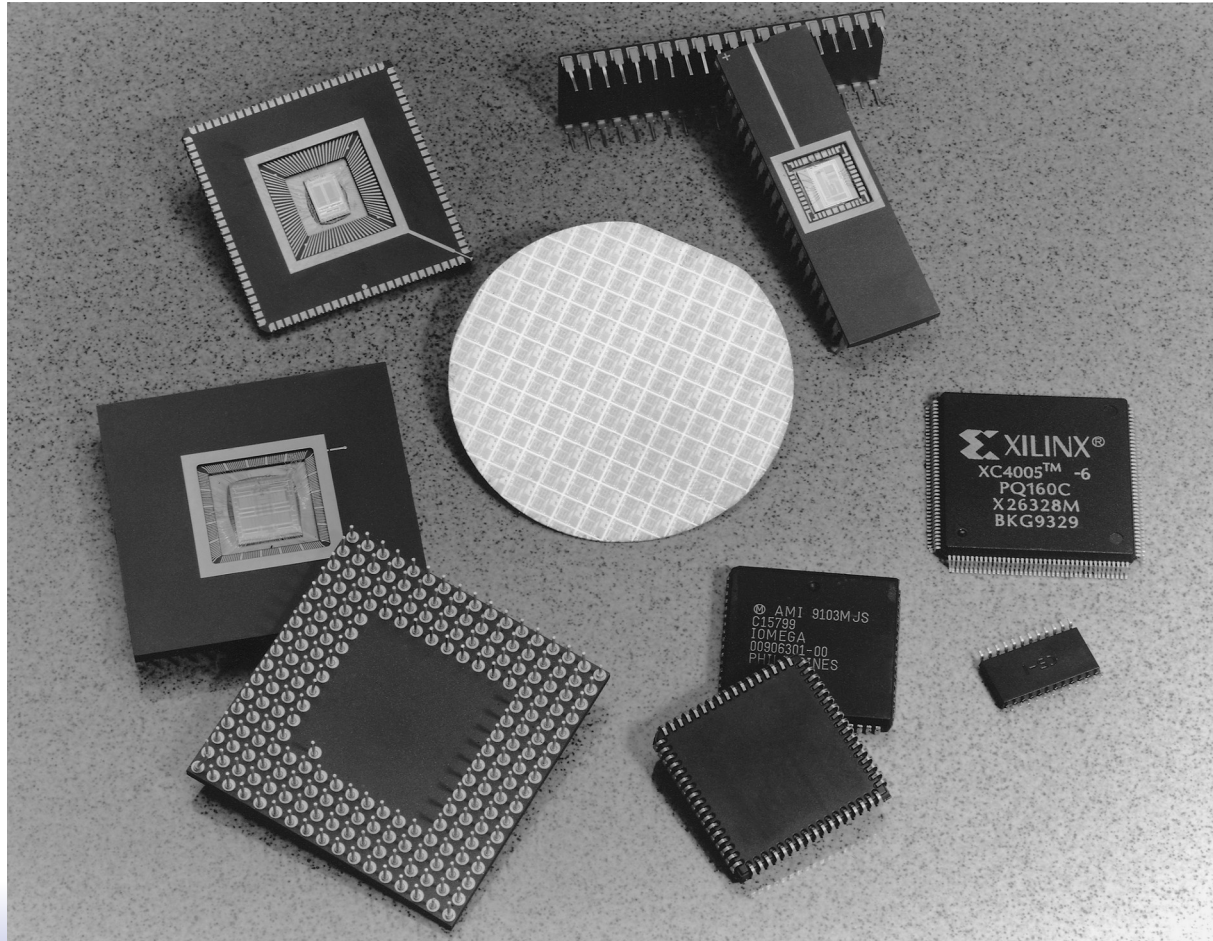


(a) Through-Hole Mounting



(b) Surface Mount

Package Types



Package Parameters

Package Type	Capacitance (pF)	Inductance (nH)
68 Pin Plastic DIP	4	35
68 Pin Ceramic DIP	7	20
256 Pin Pin Grid Array	5	15
Wire Bond	1	1
Solder Bump	0.5	0.1

Typical Capacitances and Inductances of Various Package and Bonding Styles (from [Sze83])

Multi-Chip Modules

